

**Vishay Siliconix** 

## N-Channel 60 V (D-S) 175 °C MOSFET

## DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C<sub>gd</sub> model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

# SUBCIRCUIT MODEL SCHEMATIC

### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics



#### Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	2.8	-	V
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 6 \text{ A}$	0.010	0.010	Ω
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 5 \text{ A}$	0.012	0.012	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 6 \text{ A}$	27	25	S
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1.7 A	0.72	0.72	V
Dynamic <sup>b</sup>					
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	2540	2531	pF
Output Capacitance	C <sub>oss</sub>		384	382	
Reverse Transfer Capacitance	C <sub>rss</sub>		141	153	
Total Gate Charge	Qg	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 12 \text{ A}$	41	45	nC
Gate-Source Charge	Q <sub>gs</sub>		9.9	9.9	
Gate-Drain Charge	Q <sub>gd</sub>		11.2	11.2	

Notes

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.



## **SPICE Device Model SQ4470EY**

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#### 50 15 T<sub>J</sub> = 125 °C V<sub>GS</sub> = 10 V, 9 V, 8 V, 7 V, 6 V 40 12 TJ - 55 °C I<sub>D</sub> - Drain Current (A) I<sub>D</sub> - Drain Current (A) 30 9 20 6 V<sub>GS</sub> = 5 V 10 3 = 25 °C 0 0 2 4 2 8 0 1 3 5 0 4 6 10 $\rm V_{DS}$ - Drain-to-Source Voltage (V) V<sub>GS</sub> - Gate-to-Source Voltage (V) 0.05 3500 3000 0.04 C<sub>iss</sub> R<sub>DS(on)</sub> - On-Resistance (Ω) 2500 C - Capacitance (pF) 0.03 2000 1500 0.02 V<sub>GS</sub> = 4.5 V 1000 ..... 0.01 500 C, V<sub>GS</sub> = 10 V C<sub>rss</sub> 0.00 0 10 20 30 40 5 20 25 0 50 0 10 15 30 I<sub>D</sub> - Drain Current (A) V<sub>DS</sub> - Drain-to-Source Voltage (V) 10 100 I<sub>D</sub> = 12 A 150 °C Тı 8 10 V<sub>GS</sub> - Gate-to-Source Voltage (V) $V_{DS} = 30 V$ I<sub>S</sub> - Source Current (A) 25 °C 6 4 0.1 2 0.01 0.001 0 0 10 20 30 40 50 0 0.2 0.4 0.6 0.8 1.0 1.2 Q<sub>g</sub> - Total Gate Charge (nC) V<sub>SD</sub> - Source-to-Drain Voltage (V)

## COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted)

#### Note

Dots and squares represent measured data.

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